

CORRECTION

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Correction: High density and patternable growth of silicon, germanium and alloyed SiGe nanowires by a rapid anneal protocol

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Correction for 'High density and patternable growth of silicon, germanium and alloyed SiGe nanowires by a rapid anneal protocol' by M. Bezuidenhout et al., *J. Mater. Chem. C*, 2015, **3**, 7455–7462.

Ref. 49 of the manuscript has been updated as follows;

49 T. Kennedy, M. Bezuidenhout, K. Palaniappan, K. Stokes, M. Brandon and K. M. Ryan, *ACS Nano*, 2015, DOI: 10.1021/acsnano.5b02528.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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